

2SC5913

Silicon NPN triple diffusion mesa type

Horizontal deflection output for TV, CRT Monitor

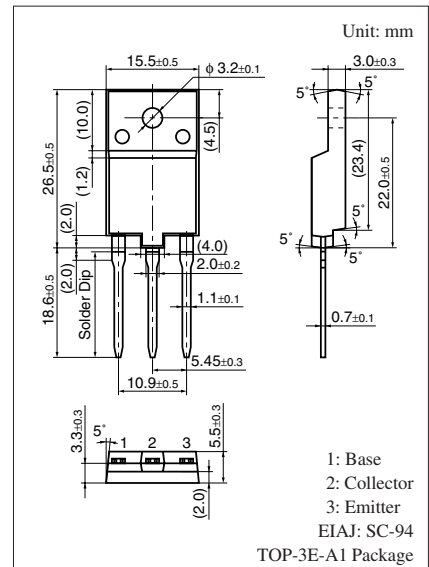
■ Features

- High breakdown voltage: $V_{CBO} \geq 1500$ V
- Wide safe operation area
- Built-in dumper diode

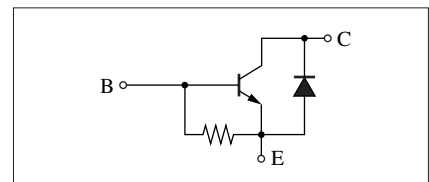
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|--------------------------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 1500 | V |
| Collector-emitter voltage (E-B short) | V_{CES} | 1500 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V |
| Base current | I_B | 3 | A |
| Collector current | I_C | 6 | A |
| Peak collector current * | I_{CP} | 9 | A |
| Collector power dissipation | P_C | 40 | W |
| | $T_a = 25^\circ\text{C}$ | 3 | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *: Non-repetitive peak collector current



Internal Connection

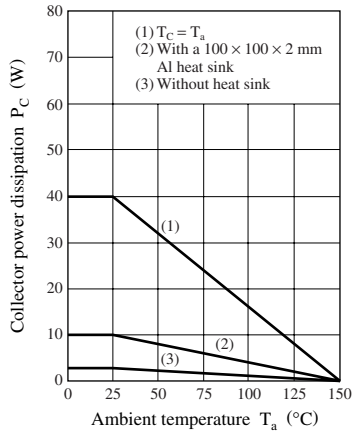


■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

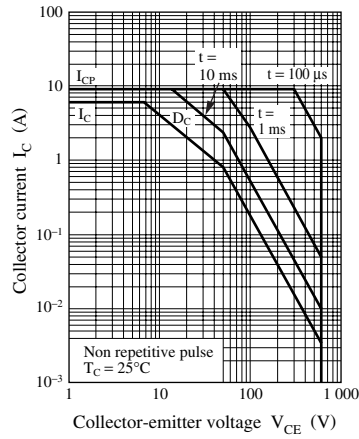
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|---|-----|-----|-----|---------------|
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 500$ mA, $I_C = 0$ | 5 | | | V |
| Forward voltage | V_F | $I_F = 3$ A | | | -2 | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 1000$ V, $I_E = 0$ | | | 50 | μA |
| | | $V_{CB} = 1500$ V, $I_E = 0$ | | | 1 | mA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 5$ V, $I_C = 3$ A | 5 | | 10 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 3$ A, $I_B = 0.75$ A | | | 2.5 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_C = 3$ A, $I_B = 0.75$ A | | | 1.5 | V |
| Transition frequency | f_T | $V_{CE} = 10$ V, $I_C = 0.1$ A, $f = 0.5$ MHz | | 3 | | MHz |
| Storage time | t_{stg} | $I_C = 3$ A, Resistance loaded | | | 5.0 | μs |
| Fall time | t_f | $I_{B1} = 0.75$ A, $I_{B2} = -1.5$ A | | | 0.5 | μs |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

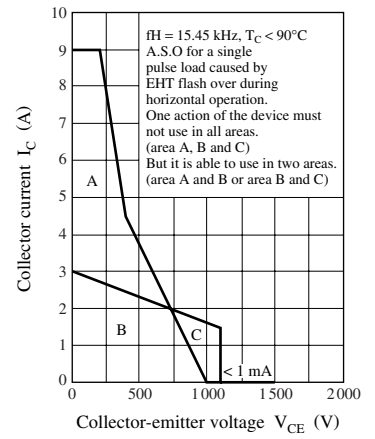
$P_C - T_a$



Safe operation area



Safe operation area (Horizontal operation)



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